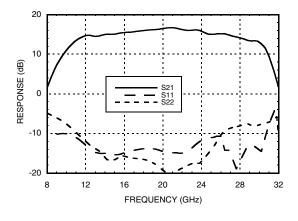


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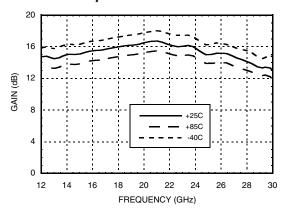


GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 12 - 30 GHz

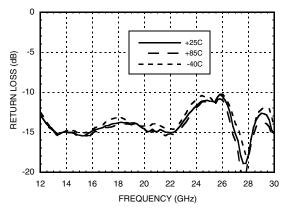
Broadband Gain & Return Loss



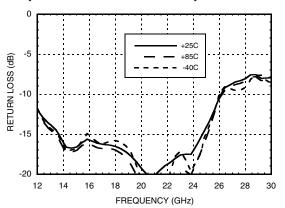
Gain vs. Temperature



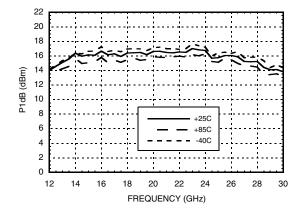
Input Return Loss vs. Temperature



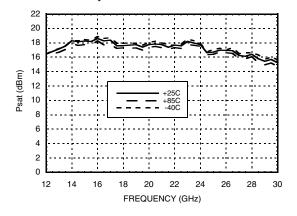
Output Return Loss vs. Temperature



P1dB vs. Temperature



Psat vs. Temperature



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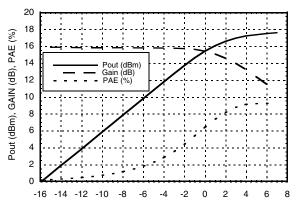
For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106 Phone: 781-329-4700 • Order online at www.analog.com Application Support: Phone: 1-800-ANALOG-D



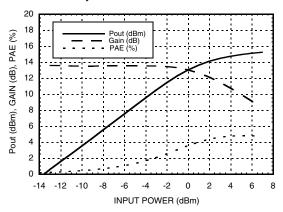


GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 12 - 30 GHz

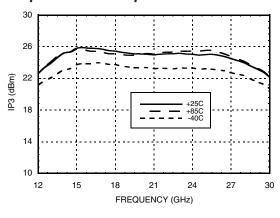
Power Compression @ 18 GHz



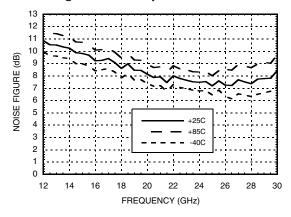
Power Compression @ 30 GHz



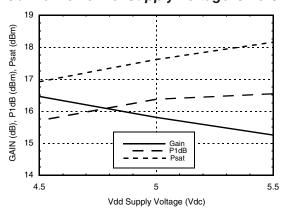
Output IP3 vs. Temperature



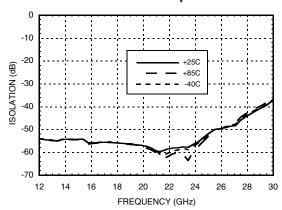
Noise Figure vs. Temperature



Gain & Power vs. Supply Voltage @ 18 GHz



Reverse Isolation vs. Temperature





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GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 12 - 30 GHz

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+5.5 Vdc
RF Input Power (RFIN)(Vdd = +5Vdc)	+10 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 10 mW/°C above 85 °C)	0.92 W
Thermal Resistance (channel to ground paddle)	98 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+4.5	99
+5.0	100
+5.5	101

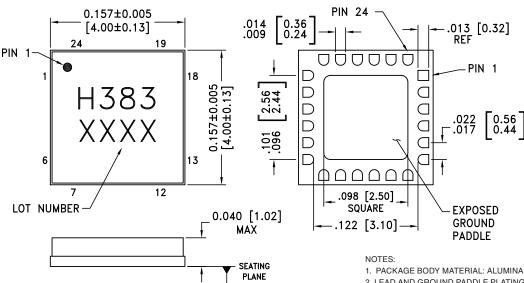
Note: Amplifier will operate over full voltage ranges shown above



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing

BOTTOM VIEW



-C-

- 2. LEAD AND GROUND PADDLE PLATING: 30-80 MICROINCHES GOLD OVER 50 MICROINCHES MINIMUM NICKEL.
- 3. ALL DIMENSIONS ARE IN INCHES [MM]
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM -C-
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC383LC4	Alumina, White	Gold over Nickel	MSL3 [1]	H383 XXXX

^[1] Max peak reflow temperature of 260 °C

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^{[2] 4-}Digit lot number XXXX





GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 12 - 30 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4 - 15, 17, 18, 20 - 24	N/C	No connection required. These pins may be connected to RF/DC ground without affecting performance if using grounded coplanar wave guide transmission lines.	
3	RFIN	This pad is AC coupled and matched to 50 Ohms.	
16	RFOUT	This pad is AC coupled and matched to 50 Ohms.	— —○ RFOUT
19	Vdd	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μF are required.	Vdd ———————————————————————————————————
	GND	Package base has an exposed metal ground that must be connected to RF/DC ground. Vias under the device are required	GND

Application Circuit

Component	Value			
C1	100 pF		Vdo	d
C2	1,000 pF		P	
C3	2.2 μF		-	
		RFIN	3	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

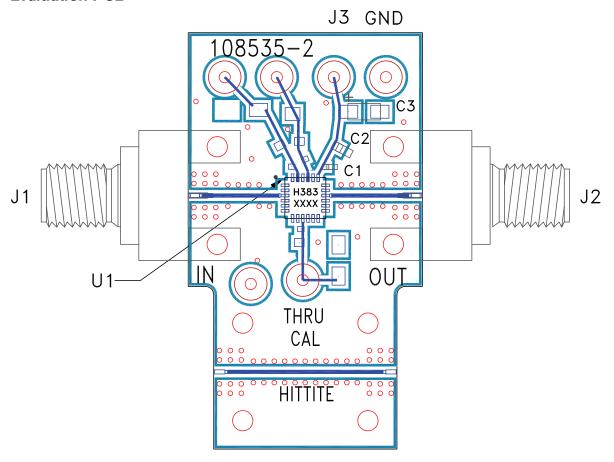


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GaAs PHEMT MMIC MEDIUM POWER AMPLIFIER, 12 - 30 GHz

Evaluation PCB



List of Materials for Evaluation PCB 122198 [1]

Item	Description
J1, J2	2.92 mm PCB mount K-connector
J3, J4	DC Pin
C1	100 pF capacitor, 0402 pkg.
C2	1,000 pF Capacitor, 0603 pkg.
C3	2.2µF Capacitor, Tantalum
U1	HMC383LC4 Amplifier
PCB [2]	108535 Evaluation PCB

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

^[2] Circuit Board Material: Rogers 4350.